

1920AB12

12 Watts, 25 Volts, Class AB Personal 1930 - 1990 MHz

GENERAL DESCRIPTION

The 1920AB12 is a COMMON EMITTER transistor capable of providing 12 Watts of Class AB, RF output power over the band 1930-1990 MHz. This transistor is specifically designed for **PERSONAL COMMUNICATIONS BASE STATION** amplifier applications. It includes Input prematching and utilizes Gold metalization and HIGH VALUE EMITTER ballasting to provide high reliability and supreme ruggedness. .

ABSOLUTE MAXIMUM RATINGS

Maximum Power Dissipation @ 25°C 46 Watts

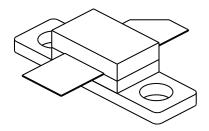
Maximum Voltage and Current

BVcesCollector to Emitter Voltage55 VoltsLvceoCollector to Emitter Voltage27 VoltsBVeboEmitter to Base Voltage3.5 VoltsIcCollector Current3.5 Amps

Maximum Temperatures

Storage Temperature $-65 \text{ to} + 150^{\circ}\text{C}$ Operating Junction Temperature $+200^{\circ}\text{C}$

CASE OUTLINE 55CT, STYLE 2 COMMON EMITTER



ELECTRICAL CHARACTERISTICS @ 25 °C

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Pout Pin Pg η _c VSWR ₁	Power Out Power Input Power Gain Collector Efficiency Load Mismatch Tolerance	F=1990 MHz Vce = 25 Volts Icq = 130 mAmps As Above	12 7.5	8.0 43	2.2	Watt Watt dB %

BVces	Collector to Emitter Breakdown	Ic = 50 mA	55			Volts
LVceo	Collector to Emitter Breakdown	Ic = 50 mA	27			Volts
BVebo	Emitter to Base Breakdown	Ie = 10 mA	3.5			Volts
Ices	Collector Leakage Current	Vce = 27 Volts			3	mA
$\mathbf{h}_{ ext{FE}}$	DC - Current Gain	Vce = 5 V, Ic = 0.5 A	20		100	
Cob	Output Capacitance	F = 1 MHz, Vcb = 28 V		12		pF
θјс	Thermal Resistance	$Tc = 25^{\circ}C$			3.8	°C/W

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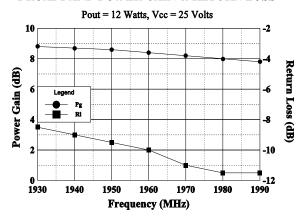
GHz Technology Inc. 3000 Oakmead Village Drive, Santa Clara, CA 95051-0808 Tel. 408 / 986-8031 Fax 408 / 986-8120

CHz TECHNOLOGY RF-MICROWAVE SILICON POWER TRANSISTORS

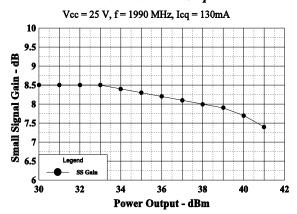
Typical Performance

1920AB12

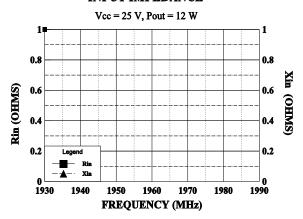
BROADBAND POWER GAIN & RETURN LOSS



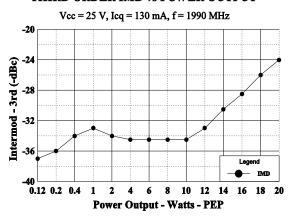
Power Gain vs Power Output



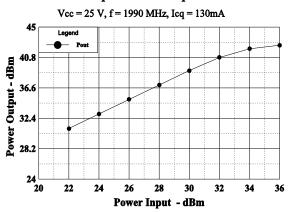
INPUT IMPEDANCE



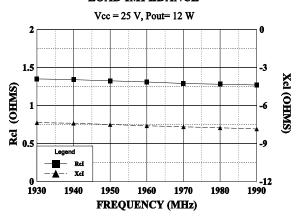
THIRD ORDER IMD vs POWER OUTPUT

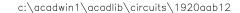


Power Output vs Power Input - dBm



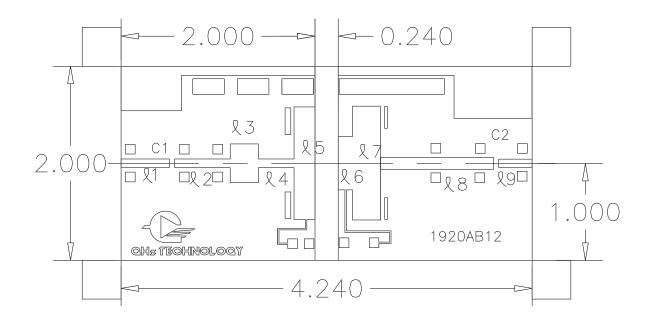
LOAD IMPEDANCE







DATE APPROVED



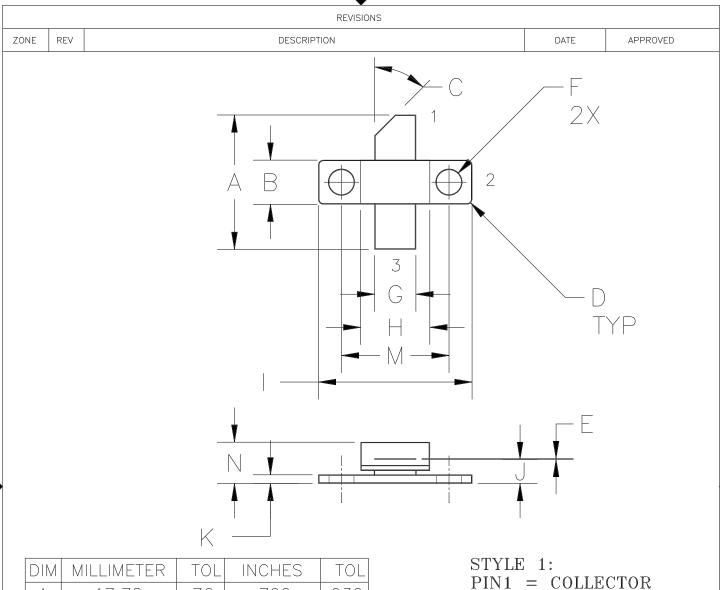
RNO.	X DIM	Y DIM
1	.500	.088
2	.575	.088
3	.290	.380
4	.370	.088
5	.215	1.160
6	.150	.550
7	.290	1.174
8	1.165	.120
9	.345	.088

C1,C2=100pf ATC 1/32" PTFE glass Er=2.5



CAGE	DWG NO.	1	920AR12		REV	7
OPJR2			9ZUAD IZ			<u> </u>
	SCALE 1/	1 DATE	19SEP95	SHEE	ET 1	of 1

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DIM	MILLIMETER	TOL	INCHES	TOL
А	17.78	.76	.700	.030
В	5.84	.13	.230	.005
С	45°	5°	45°	5°
D	0.63R	.13	.025R	.005
Е	0.13	.02	.005	.001
F	3.30 DIA	.13	.130 DIA	.005
G	5.46	.13	.215	.005
Н	9.14	.13	.360	.005
	20.32	.13	.800	.005
J	3.17	.25	.125	.010
K	1.14	.13	.045	.005
М	14.22	.13	.560	.005
N	5.46	REF	.215	REF

2 = BASE

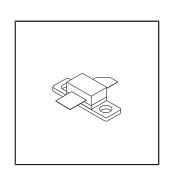
3 = EMITTER

STYLE 2:

PIN1 = COLLECTOR

2 = EMITTER

3 = BASE





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cage 0PJR2	DWG NO.	55CT		REV $f A$
	SCALE	2/1	SHEET	·